Abstracts

Design Techniques for GaAs MESFET Switches

G.J. Gardiner, M.W. Geen and D.C. Smith. "Design Techniques for GaAs MESFET Switches." 1989 MTT-S International Microwave Symposium Digest 89.1 (1989 Vol. I [MWSYM]): 405-408.

A three port bias dependent model for a switch FET is presented. The importance of a three port model is highlighted. Large signal behaviour of a MESFET switch in its ON and OFF states is discussed. The effect of gate bias resistor and bias potential is illustrated. Simple equations and techniques are presented which enable estimates of power performance of complex switches to be made prior to detailed non-linear analysis.

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